Unit: mm

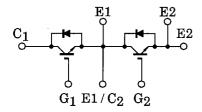
TOSHIBA GTR Module Silicon N Channel IGBT

MG120V2YS40

High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance
- Includes a complete half bridge in one package.
- Enhancement-mode
- High speed : $t_f = 1.5\mu s \text{ (max) (IC} = 120A)$ $t_{rr} = 0.6\mu s \text{ (max) (IF} = 120A)$

Equivalent Circuit



Maximum Ratings (Ta = 25°C)

4-Ø6.6±0.3 4-FAST-ON-TAB #110 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0
JEDEC —
JEITA —
TOSHIBA 2-109C1A
Weight: 430g (typ.)

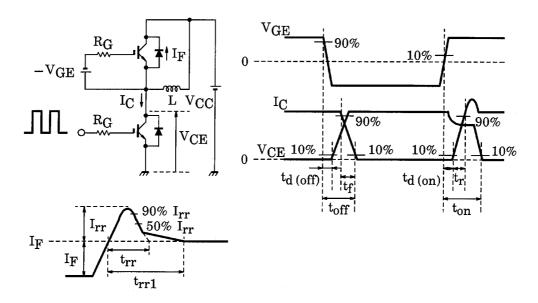
Weight: 430g (typ.)

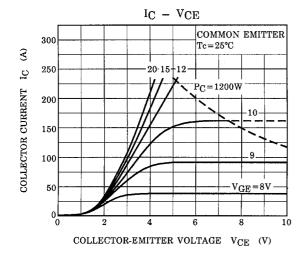
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1700	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	Ic	120	Α	
	1ms	I _{CP}	240		
Forward current	DC	lF	120	Α	
	1ms	I _{FM}	240		
Collector power dissipation (Tc = 25°C)		PC	1200	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	4000 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

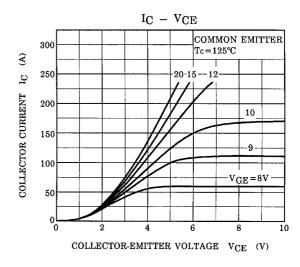
Electrical Characteristics (Ta = 25°C)

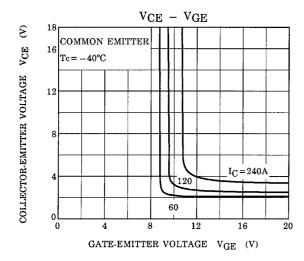
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0	_	_	±100	nA
Collector cut-off current		I _{CES}	V _{CE} = 1700V, V _{GE} = 0	_	_	1	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 120mA, V _{CE} = 5V	4.0	_	8.0	V
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 120A, V _{GE} = 15V	_	3.2	4.5	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	16400	_	pF
Switching time	Turn-on delay time	t _{d(on)}	Inductive load $V_{CC}=900V$ $I_{C}=120A$ $V_{GE}=\pm15V$ $R_{G}=4.7\Omega$ (Note 1)	_	0.1	_	μs
	Rise time	t _r		_	0.1	_	
	Turn-on time	t _{on}		_	0.5	_	
	Turn-off delay time	t _{d(off)}		_	0.4	_	
	Fall time	t _f		_	0.5	1.5	
	Turn-off time	t _{off}		_	1.0	_	
Forward voltage		V _F	I _F = 120A, V _{GE} = 0	_	3.5	4.5	V
Reverse recovery time		t _{rr}	I _F = 120A, V _{GE} = -15V di / dt = 500A / µs (Note 1)	_	0.3	0.6	μs
Thermal resistance		R _{th (j-c)}	Transistor stage	_	_	0.104	°C/W
			Diode stage	_	_	0.25	

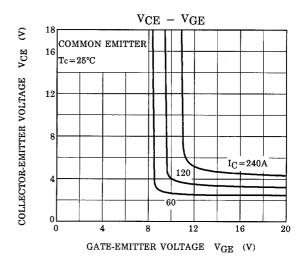
Note 1: Switching time and reverse recovery time test circuit & timing chart

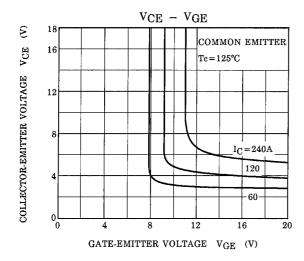


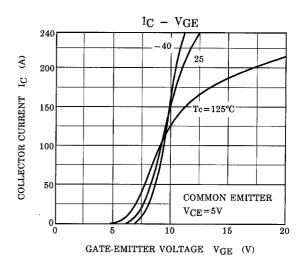


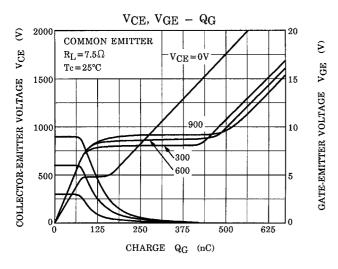


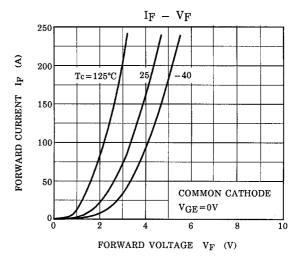


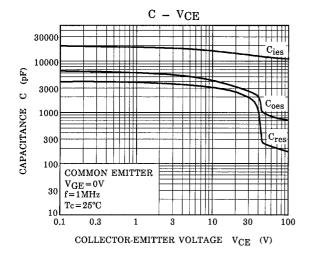


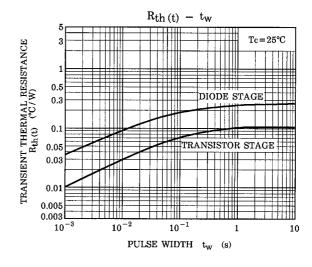


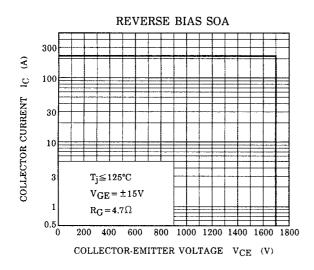












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